Emine Ozturk

List of Publications by Year
in descending order

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61	1,082	361045	454577
papers	citations	20 h-index	30 g-index

62	62	62	299
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Nonlinear intersubband absorption and refractive index change in n-type Î´-doped GaAs for different donor distributions. European Physical Journal Plus, 2015, 130, 1.	1.2	92
2	The dependence of the intersubband transitions in square and graded QWs on intense laser fields. Solid State Communications, 2004, 132, 497-502.	0.9	49
3	Intersubband transitions in an asymmetric double quantum well. Superlattices and Microstructures, 2007, 41, 36-43.	1.4	48
4	Electric field and intense laser field effects on the intersubband optical absorption in a graded quantum well. Journal Physics D: Applied Physics, 2005, 38, 935-941.	1.3	43
5	Nonlinear optical absorption in graded quantum wells modulated by electric field and intense laser field. European Physical Journal B, 2010, 75, 197-203.	0.6	40
6	Nonlinear intersubband absorption and refractive index changes in square and graded quantum well modulated by temperature and Hydrostatic pressure. Journal of Luminescence, 2013, 134, 42-48.	1.5	40
7	Nonlinear intersubband transitions in a parabolic and an inverse parabolic quantum well under applied magnetic field. Journal of Luminescence, 2014, 145, 387-392.	1.5	36
8	The electric field effects on intersubband optical absorption of Si Î´-doped GaAs layer. Solid State Communications, 2003, 126, 605-609.	0.9	33
9	Effect of magnetic fields on the linear and nonlinear intersubband optical absorption coefficients and refractive index changes in square and graded quantum wells. Superlattices and Microstructures, 2010, 48, 312-320.	1.4	33
10	Intersubband optical absorption in double quantum well under intense laser field. EPJ Applied Physics, 2006, 35, 1-5.	0.3	31
11	Nonlinear intersubband transitions in different shaped quantum wells under intense laser field. Superlattices and Microstructures, 2015, 82, 303-312.	1.4	29
12	The self-consistent calculation of Si Î´-doped GaAs structures. Applied Physics A: Materials Science and Processing, 2001, 73, 749-754.	1.1	28
13	Si Î´-doped GaAs structure with different dopant distribution models. Journal of Applied Physics, 2002, 91, 2118-2122.	1.1	28
14	The effects of hydrostatic pressure on the nonlinear intersubband transitions and refractive index changes of different QW shapes. Optics Communications, 2012, 285, 5223-5228.	1.0	28
15	Linear and nonlinear intersubband optical absorption coefficient and refractive index change in n-type Î´-doped GaAs structure. Optics Communications, 2013, 294, 361-367.	1.0	28
16	Intersubband transitions for single, double and triple Si Â-doped GaAs layers. Journal Physics D: Applied Physics, 2003, 36, 2457-2464.	1.3	24
17	Simultaneous effects of the intense laser field and the electric field on the nonlinear optical properties in GaAs/GaAlAs quantum well. Optics Communications, 2014, 332, 136-143.	1.0	24
18	Electronic subband of single SiÎ´-doped GaAs structures. Superlattices and Microstructures, 2000, 28, 35-45.	1.4	23

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19	Optical intersubband transitions in double Si <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si10.gif" display="inline" overflow="scroll"><mml:mi>Î´</mml:mi></mml:math>-doped GaAs under an applied magnetic field. Superlattices and Microstructures, 2009, 46, 752-759.	1.4	21
20	Electronic properties of Si Î´-doped GaAs under an applied electric field. Semiconductor Science and Technology, 2001, 16, 421-426.	1.0	20
21	Electric field effect on the nonlinear optical absorption in double semi-graded quantum wells. Optics Communications, 2013, 305, 228-235.	1.0	19
22	Intersubband transitions in quantum wells under intense laser field. Applied Physics A: Materials Science and Processing, 2005, 80, 541-544.	1.1	18
23	Resonant peaks of the linear optical absorption and rectification coefficients in GaAs/GaAlAs quantum well: Combined effects of intense laser, electric and magnetic fields. International Journal of Modern Physics B, 2015, 29, 1550030.	1.0	17
24	Linear and nonlinear optical absorption coefficient and electronic features of triple GaAlAs/GaAs and GaInAs/GaAs quantum wells depending on barrier widths. Optik, 2019, 180, 394-405.	1.4	17
25	Linear and nonlinear optical absorption in different graded quantum wells modulated by intense laser field. Superlattices and Microstructures, 2012, 52, 1010-1019.	1.4	16
26	The effect of barrier width on the electronic properties of double GaAlAs/GaAs and GaInAs/GaAs quantum wells. Journal of Molecular Structure, 2018, 1156, 726-732.	1.8	16
27	Intersubband optical absorption coefficients and refractive index changes in triple quantum well with different well shapes. EPJ Applied Physics, 2010, 51, 10303.	0.3	14
28	Intersubband transitions and refractive index changes in coupled double quantum well with different well shapes. Superlattices and Microstructures, 2011, 50, 350-358.	1.4	14
29	Electric and intense laser field effect on the electronic properties of Ga1â^'xAlxAs/GaAs and Ga1â^'xInxAs/GaAs semi-parabolic quantum wells. Laser Physics, 2016, 26, 096102.	0.6	13
30	Nonlinear intersubband transitions in asymmetric double quantum wells as dependent on intense laser field. Optical and Quantum Electronics, 2016, 48, 1.	1.5	13
31	The triple Si Î´-doped GaAs structure. Applied Physics A: Materials Science and Processing, 2005, 80, 167-171.	1.1	12
32	Effect of Magnetic Field on a p-Type Î´-Doped GaAs Layer. Chinese Physics Letters, 2010, 27, 077302.	1.3	12
33	Interband transitions dependent on indium concentration inÂGa1â^'xInxAs/GaAs asymmetric triple quantum wells. International Journal of Modern Physics B, 2018, 32, 1850052.	1.0	11
34	Electronic properties of two coupled SiÎ´-doped GaAs structures. EPJ Applied Physics, 2003, 21, 91-95.	0.3	11
35	The effect of the donor distribution on the electronic structure of two coupled Si Î´-doped layers in GaAs. Physica B: Condensed Matter, 2003, 334, 1-8.	1.3	10
36	Intersubband optical absorption in SiÎ´-doped GaAs for the donor distribution and thickness as dependent on the applied electric field. EPJ Applied Physics, 2004, 25, 3-9.	0.3	10

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37	Intersubband optical absorption of double Si Î´-doped GaAs layers. Superlattices and Microstructures, 2004, 35, 95-104.	1.4	10
38	Depending on the intense laser field of the nonlinear optical rectification, second and third harmonic generation in asymmetric parabolic-step and inverse parabolic-step quantum wells. Physica Scripta, 2019, 94, 115809.	1.2	10
39	Electronic structure of two coupled Si Î´-doped GaAs as dependent on the donor thickness. Applied Physics A: Materials Science and Processing, 2003, 77, 427-431.	1.1	9
40	The variation of electronic properties with the doping concentration of modulation-doped AlxGa1â^'xAsâ€“GaAs double quantum wells. Superlattices and Microstructures, 2007, 41, 22-28.	1.4	9
41	Linear and total intersubband transitions in the step-like GaAs/GaAlAs asymmetric quantum well as dependent on intense laser field. European Physical Journal Plus, 2015, 130, 1.	1.2	9
42	The effect of intense laser field on the nonlinear optical features in asymmetric multiple step and inverse V-shaped multiple step quantum wells. Laser Physics, 2019, 29, 105401.	0.6	9
43	Intense laser field effect on the nonlinear optical properties of triple quantum wells consisting of parabolic and inverse-parabolic quantum wells. Laser Physics, 2022, 32, 035404.	0.6	9
44	Linear and nonlinear optical properties of a superlattice with periodically increased well width under electric and magnetic fields. , 2022, 166, 207225.		9
45	INTERSUBBAND OPTICAL ABSORPTION IN QUANTUM WELLS UNDER APPLIED ELECTRIC AND INTENSE LASER FIELDS. Surface Review and Letters, 2004, 11, 297-303.	0.5	8
46	Comparison of asymmetric double parabolic-inversed parabolic quantum wells for linear optical (1â€“2) transition. Optik, 2017, 139, 256-264.	1.4	8
47	Linear and nonlinear optical properties of semi-elliptical InAs quantum dots: Effects of wetting layer thickness and electric field. Thin Solid Films, 2022, 755, 139322.	0.8	8
48	Subband structure ofp-typeÎ´-doped GaAs as dependent on the acceptor concentration and the layer thickness. EPJ Applied Physics, 2008, 41, 195-200.	0.3	7
49	Effect of the intense laser field on the valance band for Ga1â^'xAlxAs/GaAs heterostructure. Superlattices and Microstructures, 2009, 45, 16-21.	1.4	7
50	Nonlinear Intersubband Transitions in Square and Graded Quantum Wells Modulated by Intense Laser Field. Chinese Physics Letters, 2014, 31, 127301.	1.3	7
51	Linear and nonlinear optical absorption coefficients and refractive index changes in double parabolic-square quantum well as dependent on intense laser field. European Physical Journal Plus, 2015, 130, 1.	1.2	7
52	Depending on the electric and magnetic field of the linear optical absorption and rectification coefficient in triple quantum well. Optical and Quantum Electronics, 2017, 49, 1.	1.5	7
53	Influence of temperature on the electronic properties of SiÎ´-doped GaAs structures. EPJ Applied Physics, 2003, 21, 97-101.	0.3	7
54	Nonlinear Optical Rectification, Second and Third Harmonic Generations in Square-Step and Graded-Step Quantum Wells under Intense Laser Field. Chinese Physics Letters, 2019, 36, 067801.	1.3	6

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55	Subband structure and band bending in symmetric modulation-doped double quantum wells. EPJ Applied Physics, 2005, 29, 27-31.	0.3	5
56	Dependence on well widths of total optical absorption coefficient of asymmetric triple GaAlAs/GaAs and GaInAs/GaAs quantum wells. International Journal of Modern Physics B, 2019, 33, 1950175.	1.0	5
57	Intersubband Transitions of Si Â-Doped GaAs Layer for Different Donor Distribution Models. Chinese Physics Letters, 2004, 21, 930-933.	1.3	2
58	Linear and nonlinear optical properties of asymmetric triple quantum wells under intense laser field. Laser Physics, 2019, 29, 055402.	0.6	2
59	Comparison of Ga1â^'xAlxAs/GaAs and Ga1â^'xInxAs/GaAs quantum wells as dependent on Al and In concentrations under intense laser field. International Journal of Modern Physics B, 2015, 29, 1550187.	1.0	1
60	Influence of an applied electric field on the electronic properties of SiÎ´-doped GaAs. EPJ Applied Physics, 2003, 24, 189-194.	0.3	0
61	Effect of an intense laser field on the holes in graded quantum wells. European Physical Journal Plus, 2013, 128, 1.	1.2	0